TANCERAM® CHIP CAPACITORS



TANCERAM® chip capacitors can replace tantalum capacitors in many applications and offer several key advantages over traditional tantalums. Because Tanceram® capacitors exhibit extremely low ESR, equivalent circuit performance can often be achieved using considerably lower capacitance values. Low DC leakage reduces current drain, extending the battery life of portable products. Tancerams® high DC breakdown voltage ratings offer improved reliability and eliminate large voltage de-rating common when designing with tantalums.

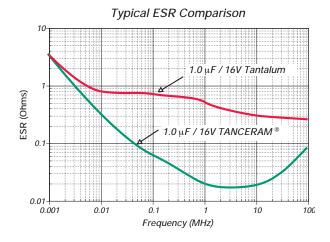
ADVANTAGES

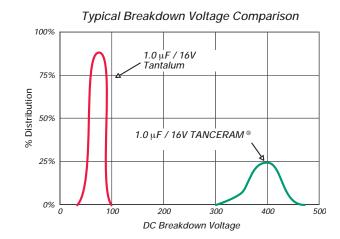
- Low ESR
- Higher Surge Voltage
- Reduced CHIP Size
- Higher Insulation Resistance
- Low DC Leakage
- Non-polarized Devices
- Improved Reliability
- Higher Ripple Current

APPLICATIONS

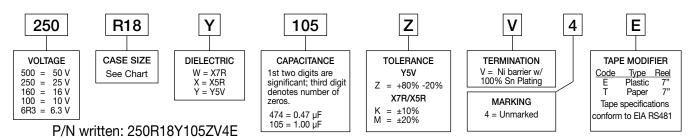
- Switching Power Supply Smoothing (Input/Output)
- DC/DC Converter Smoothing (Input/Output)

- Backlighting Inverters
- General Digital Circuits





How to Order TANCERAM®



TANCERAM® CHIP CAPACITORS

Case Size				CAPACITANCE SELECTION																						
CASE SIZE					VDC	1.0 µF		=	2.2 µF			4.7 μF				10 μF		22 µF		47 μF		100 μF				
	0402 R07	L W T E/B	Inches .040 ±.004 .020 ±.004 .025 Max .008 ±.004	(mm) (1.02 ±.10) (0.51 ±.10) (0.64) (0.20±.10)	10		*									DIELECTRIC W (X7R)										
					6.3		•			*			*			Χ	(X5R)		, ≵⊤			\			€ _{E/I}	8
	0603 L R14 T E/B		Г .035 Max.	(mm) (1.60 ±.20) (0.81 ±.20) (0.89) (.25±.13)	25			*								Υ	Y (Y5V)									
		Т			16 10		•	*	*	*																_
		E/B			6.3				*										*							
	0805	L	Inches .080 ±.010 .050 ±.010 .060 Max. .020±.010	(mm) (2.03 ±.25) (1.27 ±.25) (1.52) (0.51±.25)	25 16	•	•	•		•	*	*				•	•									_
	R15	W T			10							*				•			•							\dashv
	E/B	E/B			6.3							*				•			•							
	1206	W .062 ±.010	.125 ±.010 .062 ±.010	(mm) (3.17 ±.25) (1.57 ±.25)	25	•			•	*				•												
					16	•						•		•												_
	R18		(1.78) 1 (0.51+.3825)	10 6.3							•	•						•			•					
•	1210		Leaber	()	50	•								•		*										\dashv
		Inches L .125 ±.010 W .095 ±.010 T .110 Max.	(mm) (3.18 ±.25) (2.41 ±.25) (2.8)	25		*			*		*	•														
				16		*			*			•						•	•		•					
	S41	•	E/B .020 +.015010		10 6.3																	•			•	
				DIELECTRIC C		w	х	Υ	W	Х	Υ	W	Х	Y	W	Х	Υ	W	Х	Y	w	Х	Y	W	Х	Y
		* = NEW PART																								

ELECTRICAL

CHARACTERISTICS	X7R	X5R	Y5V							
Temperature Coefficient:	±15% (-55 to +125°C)	±15% (-55 to +85°C)	+22%, -82% (-30 to +85°C)							
Dissipation Factor:	For ≥ 50 VDC: 5% max. For ≤ 25 VDC: 10% max.	For ≥ 50 VDC: 5% max. For ≤ 25 VDC: 10% max.	For ≥ 10 VDC: 16% max. For 6.3 VDC: 20% max.							
Insulation Resistance (Min. @ 25°C, WVDC)	100 Ω F or 10 G Ω , whichever is less									
Dielectric Strength:	2.5 X WVDC, 25°C, 50mA max.									
Test Conditions:	Capacitance values \leq 22 μ F: 1.0kHz \pm 50Hz @ 1.0 \pm 0.2 Vrms Capacitance values $>$ 22 μ F: 120Hz \pm 10Hz @ 0.5V \pm 0.1 Vrms									
Other:	See page 20 for additional dielectric specifications.									